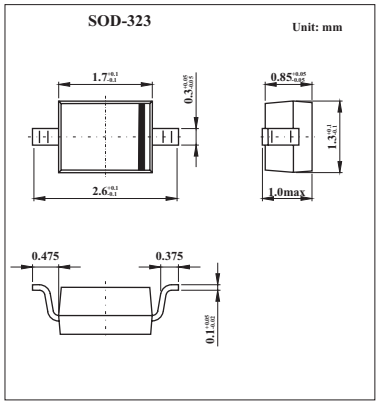
Low-Voltage Variable Capacitance Diode
BB156



Features

- Excellent linearity
- Very small plastic SMD package
- Very low series resistance.

Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
continuous reverse voltage	V_R	10	V
continuous forward current	I_F	20	mA
storage temperature	T_{stg}	-55 to 150	℃
operating junction temperature	T_j	-55 to 125	℃

Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
reverse current	I_R	V_R = 10 V			10	nA
		V_R = 10 V; T_j = 85 ℃			200	nA
diode series resistance	rs	f = 470 MHz; V_R is the value at which C_d = 9 pF		0.4	0.7	Ω
diode capacitance	C_d	V_R = 1 V,f = 1 MHz	14.4	16	17.6	pF
		V_R = 4 V,f = 1 MHz	7.6	8.6	9.6	pF
		V_R = 7.5 V,f = 1 MHz	4.2	4.8	5.4	pF
capacitance ratio	$\frac{C_{d(1V)}}{C_{d(7.5V)}}$	f = 1 MHz	2.7	3.3	3.9	

Marking

Marking	PF